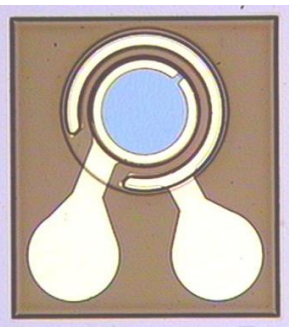
SP85-2D001 Rev 1.0

6Gbps GaAs PIN-PD Chip

Features

: Two top-side wire bond pads
: AR coated for 850 nm
: Low dark current and low capacitance
: High Data rate 4.25 / 6 Gbps

Description



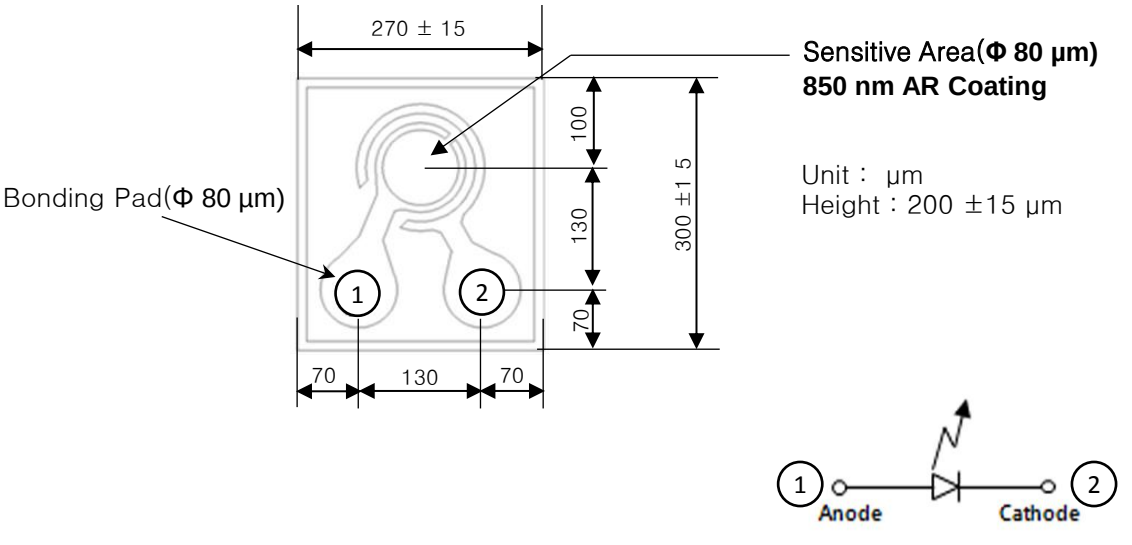
Applications

: High speed Data Communications
: Fiber Channel
: Gbps Ethernet

Absolute Maximum Ratings

Parameter	Rating
Storage Temperature	-40 to 100 ℃
Operating Temperature	-40 to 85 ℃
Forward Current	10mA
Reverse Voltage	40V

Dimensions



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Electro-Optics Characteristics (T_a=25℃ unless otherwise stated)

Parameters	Symbol	Specified			Unit	Test Conditions
		Min.	Typ.	Max.		
Sensitive Area	D		80		μm	In diameter
Responsivity	R	0.5	0.6		A/W	V_R = 1.6 V, λ= 850 nm
Dark Current	I_D		0.1	1.0	nA	V_R = 1.6 V
Breakdown Voltage	V_B	40			V	I_r = 1㎂
Capacitance	C		0.38	0.45	pF	V_R = 1.6 V, f = 1 MHz
Peak Wavelength	λ		850		nm	
Rise and Fall times	t_r/t_f			60/60	ps	V_R = 1.6 V. 20% ~ 80%
Small Signal Bandwidth	f_{-3dB}		5		GHz	V_R = 1.6 V

Notes

* Substrate : Semi-insulating GaAs
* These specifications are subject to change without notice

NOTICE	The inherent design of this component causes it to be sensitive to electrostatic discharge(ESD). To prevent ESD-induced damage and/or degradation to equipment, take normal ESD precautions when handling this product

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